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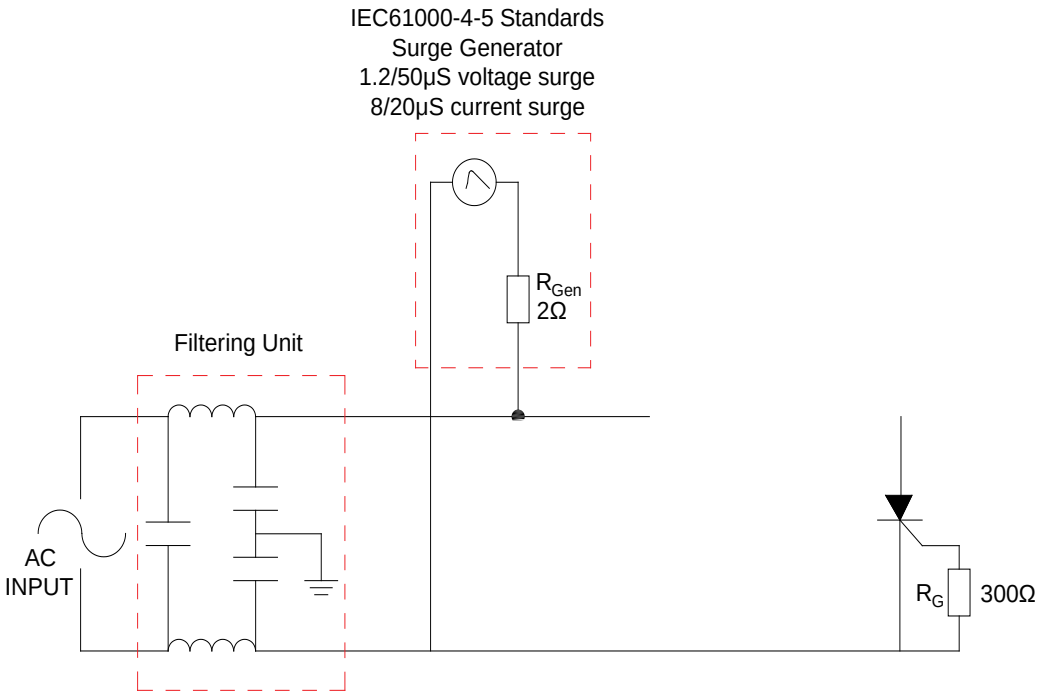
Symbol	Value	Unit
T_{stg}		
T_j	-40-125	
V_{DRM}		
V_{RRM}		
$I_{T(AV)}$	49	A
$I_{T(RMS)}$		
I_{TSM}	800	A

Average gate power dissipation (T_j=125)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	22	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	1	kV

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	V_D=12V R_L=33Ω	10	-	80	mA
V_{GT}		-	-	1.3	V
V_{GD}	V_D=V_{DRM} T_j=125 R_L=3.3kΩ	0.2	-	-	V
I_L	I_G=1.2I_{GT}	-	-	200	mA
I_H	I_T=500mA	-	-	150	mA
dV/dt	V_D=800V Gate Open T_j=125	2000	-	-	V/μs 20

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT1275Z	1200	10-80	TO-3P	30	Tube

Document Revision History

Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update
Oct.16, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

Information furnished in this docum4 (he)Tts hedTt urat1.2 (a4 (he)e)10 (dur)7 eli Hiwivhurs

at(n)10 ca(w)10 (ge)4 t(he)Tts